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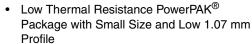
Vishay Siliconix

P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	Q _g (Typ.)		
- 20	0.019 at V _{GS} = - 4.5 V	- 16 ^e	16.2 nC		
	0.031 at V _{GS} = - 2.5 V	- 16 ^e	10.2110		

FEATURES

- Halogen-free Option Available
- TrenchFET[®] Power MOSFET

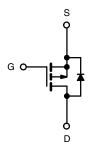




- PWM Optimized
- 100 % R_a and UIS Tested

APPLICATIONS

- DC/DC Buck Converter
- High-Side Application for Asynchronous Buck



P-Channel MOSFET

3.30 mm 3.30 mm 3.30 mm

Bottom View **Ordering Information:** Si7601DN-T1-E3 (Lead (Pb)-free)

Si7601DN-T1-GE3 (Lead (Pb)-free and Halogen-free)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V_{DS}	- 20	V	
Gate-Source Voltage		V _{GS}	± 12	
	T _C = 25 °C		- 16 ^e	
Ocation - Project Ocean - (T. 150.00)	T _C = 70 °C		- 16 ^e	
Continuous Drain Current (T _J = 150 °C)	T _A = 25 °C	I _D	- 11.5 ^{a, b}	
	T _A = 70 °C		- 9.2 ^{a, b}	Α .
Pulsed Drain Current		I _{DM}	- 40	
0 11 0 0 10 10 1	T _C = 25 °C		- 16 ^e	
Continuous Source-Drain Diode Current	T _A = 25 °C	l _S	- 3.15 ^{a, b}	
Avalanche Current	1 04	I _{AS}	15	
Single-Pulse Avalanche Energy L = 0.1 n		E _{AS}	11.25	mJ
	T _C = 25 °C		52	
M. C. B. British	T _C = 70 °C		33	
Maximum Power Dissipation	T _A = 25 °C	P _D	3.8 ^{a, b}	W
	T _A = 70 °C		2.4 ^{a, b}	
Operating Junction and Storage Temperature Range		T _J , T _{stq}	- 50 to 150	
Soldering Recommendations (Peak Temperature)		260	°C	

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. t = 10 s.
- c. See Solder Profile (http://www.vishay.com/doc?73257). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- d. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.
- e. Package limited.

Si7601DN

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THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{a, b}	t ≤ 10 s	R _{thJA}	26	33	°C/W	
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	1.9	2.4	C/VV	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.
b. Maximum under Steady State conditins is 81 °C/W.

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 20			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = - 250 μA		- 16.8		mV/°C	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			2.63			
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 0.6		- 1.6	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 100	nA	
Zana Oata Waltana Busin Oama	leas	V _{DS} = - 20 V, V _{GS} = 0 V			- 1	μΑ	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 20 V, V _{GS} = 0 V, T _J = 55 °C			- 10		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 40			Α	
Drain-Source On-State Resistance ^a	B	$V_{GS} = -4.5 \text{ V}, I_D = -11 \text{ A}$		0.016	0.0192	0	
	R _{DS(on)}	$V_{GS} = -2.5 \text{ V}, I_D = -8.9 \text{ A}$		0.025	0.0313	Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 11 A		31.7		S	
Dynamic ^b							
Input Capacitance	C _{iss}			1870		pF	
Output Capacitance	C _{oss}	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		490			
Reverse Transfer Capacitance	C _{rss}			460			
Total Cata Charge		V _{DS} = - 10 V, V _{GS} = - 5 V, I _D = - 11 A		18	27		
Total Gate Charge	Q_g			16.2	25	nC	
Gate-Source Charge	Q_{gs}	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -11 \text{ A}$		4.1			
Gate-Drain Charge	Q_{gd}			4.8			
Gate Resistance	R_{g}	f = 1 MHz		6.1	9.2	Ω	
Turn-On Delay Time	t _{d(on)}			18	27		
Rise Time	t _r	$V_{DD} = -10 \text{ V}, R_{L} = 1.09 \Omega$		112	168	ns	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong -9.2 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 1 \Omega$		53	80		
Fall Time	t _f		80		120		
Drain-Source Body Diode Characterist	ics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 16	А	
Pulse Diode Forward Current ^a	I _{SM}				- 40		
Body Diode Voltage	V _{SD}	I _S = - 6 A		- 0.8	- 1.2	V	
Body Diode Reverse Recovery Time				42	63	ns	
Body Diode Reverse Recovery Charge				25.2	38	nC	
Reverse Recovery Fall Time				14		ne	
Reverse Recovery Rise Time	t _b			28		ns	

Notes:

a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$

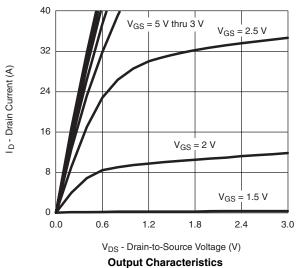
b. Guaranteed by design, not subject to production testing.

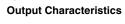
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

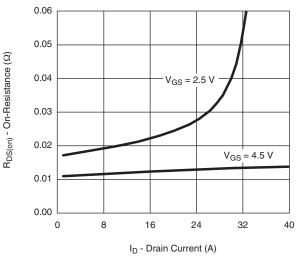


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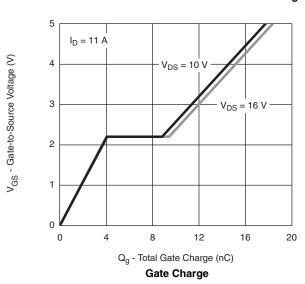
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

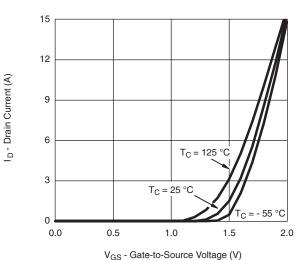




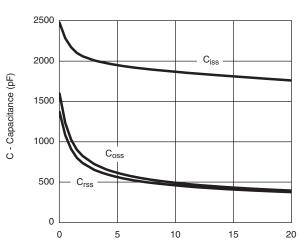


On-Resistance vs. Drain Current and Gate Voltage

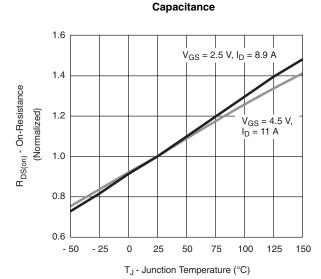




Transfer Characteristics



V_{DS} - Drain-to-Source Voltage (V)



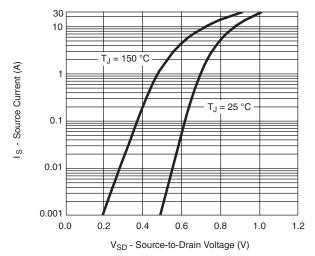
On-Resistance vs. Junction Temperature

Si7601DN

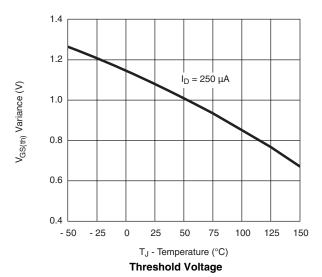
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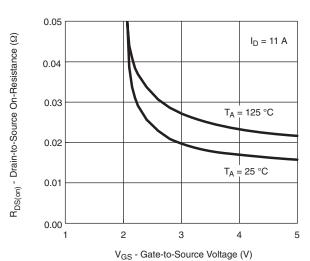
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

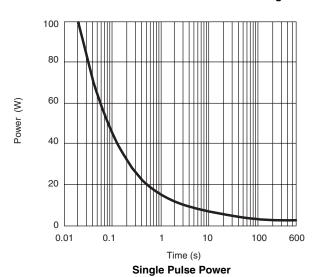


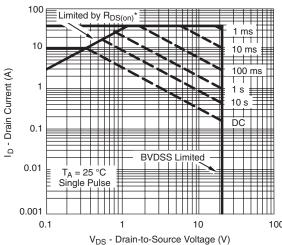
Source-Drain Diode Forward Voltage





On-Resistance vs. Gate-to-Source Voltage





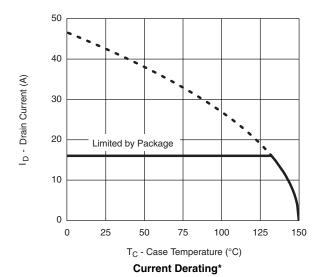
* V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified

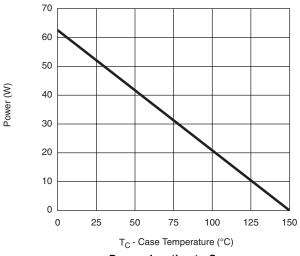
Safe Operating Area, Junction-to-Ambient



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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





Power, Junction-to-Case

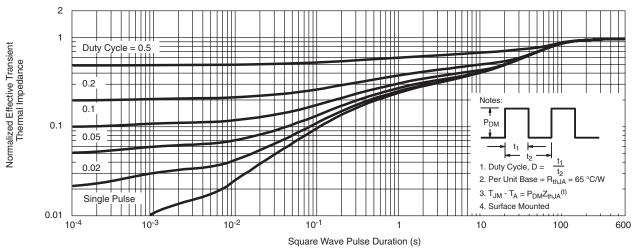
^{*} The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

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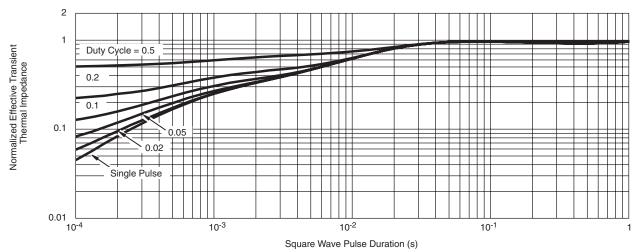
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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